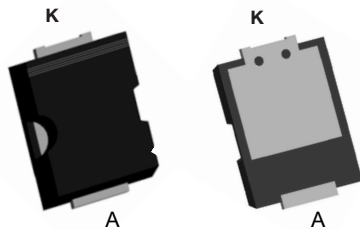


Trench MOS Barrier Schottky Rectifier

TSP8L60P6

SMP6



Cathode K  Anode A

Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (TJ = 25°C unless otherwise noted)

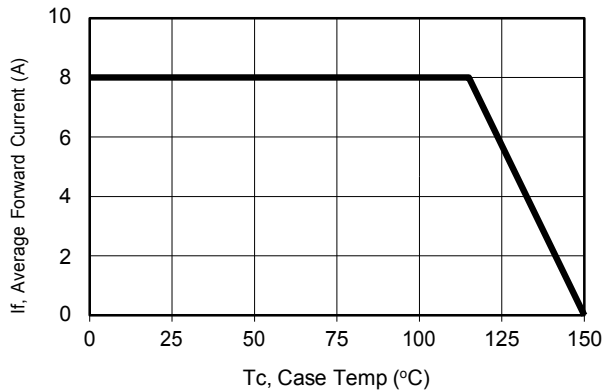
Parameter		Symbol	Limit		Unit
Maximum repetitive peak reverse voltage		VRRM	60		V
Maximum average forward rectified current		IF(AV)	8.0		A
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode		IFSM	150		A
Operating junction and storage temperature range		TJ, TSTG	-50 to +150		°C
Typical thermal resistance per diode(Mounted on FR-4 PCB)		RθJC	25		°C/W
Instantaneous forward voltage per diode			TYP.	MAX.	V
	IF=2A	TJ=25°C	0.36	0.42	
	IF=2A	TJ=125°C	0.28	-	
	IF=8A	TJ=25°C	0.51	0.53	
	IF=8A	TJ=125°C	0.46	-	
Instantaneous reverse current per diode at rated reverse voltage		TJ=25°C	10	100	uA
		TJ=125°C	20	-	mA

Notes:

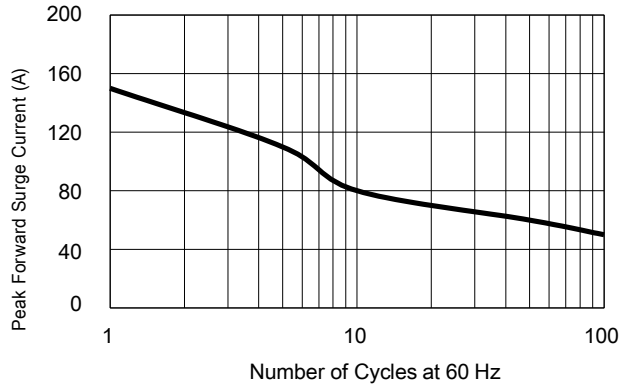
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

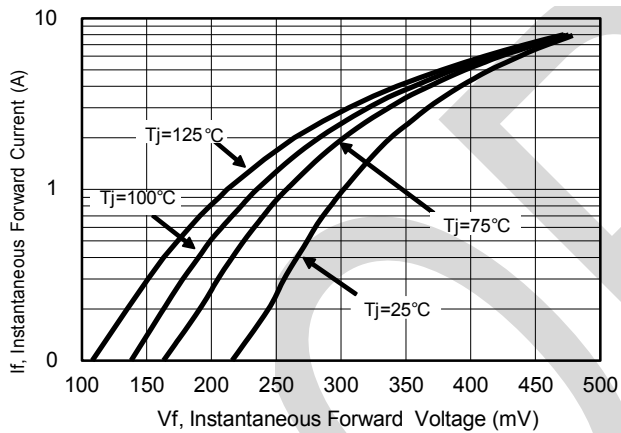
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



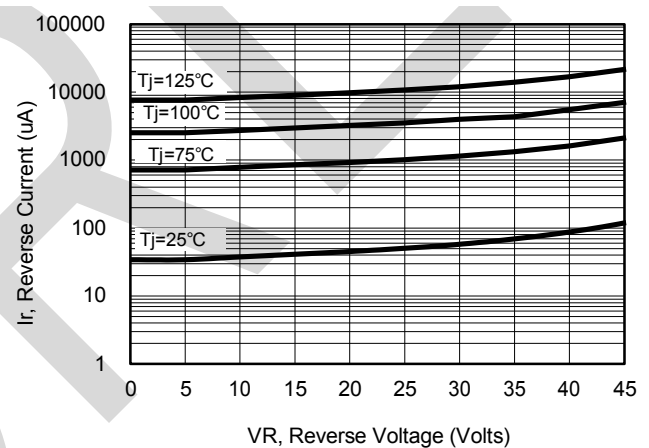
Current Derating, Case



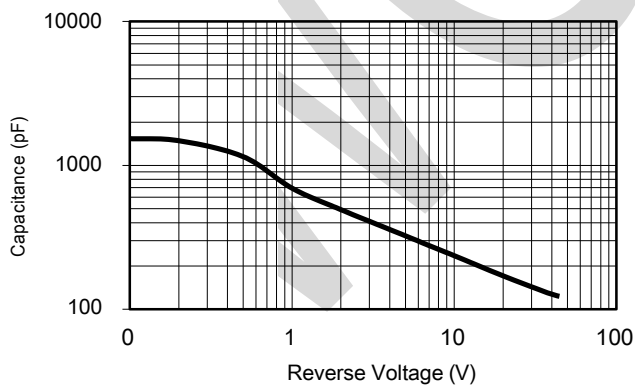
Maximum Repetitive Surge Current



Typical Forward Voltage



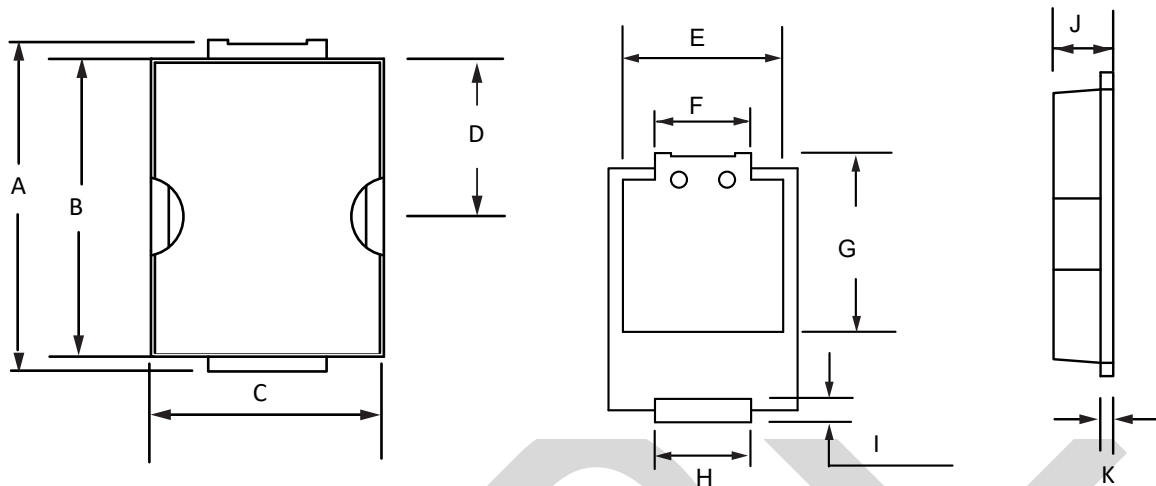
Typical Reverse Current



Typical Junction Capacitance

PACKAGE OUTLINE DIMENSIONS

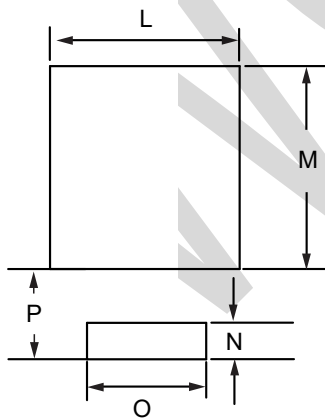
SMP6



SMP6 mechanical data

UNIT		A	B	C	D	E	F	G	H	I	J	K
mm	max	8.6	7.75	6.1	4.2	5.2	3.2	5.68	3.2	0.93	1.85	0.45
	min	8.0	7.35	5.7	3.8	4.8	2.8	5.28	2.8	0.53	1.45	0.25
mil	max	338.5	305.1	240.1	165.3	204.7	126.0	223.6	126.0	36.6	72.8	17.7
	min	314.9	289.3	224.4	149.6	188.9	110.2	207.8	110.2	20.8	57.1	9.8

SMP6 Suggested Pad Layout



UNIT		L	M	N	O	P
mm	min	5.40	5.78	1.0	3.4	1.8
mil	min	212.6	227.5	39.3	133.8	70.8